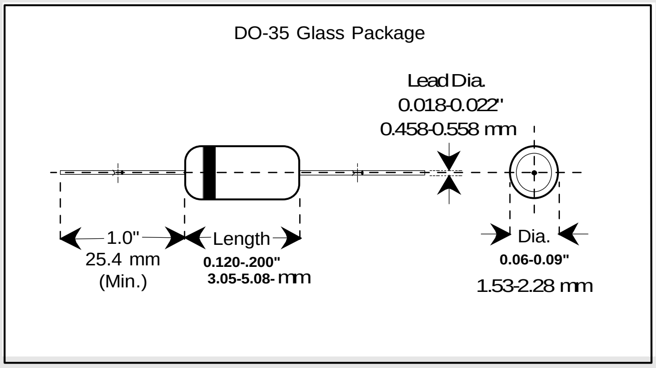
Silicon Switching Diode | 1N4148 or 1N4148-1 | DO-35 Glass Package

Applications

Used in general purpose applications,where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Hermetic Glass Body
- Available up to JANTXV-1 levels
- "S" level screening available to Source Control Drawings-



Maximum Ratings	**Symbol**	**Value**	**Unit**
Peak Inverse Voltage	PIV	100 (Min).	Volts
Average Rectified Current	Iavg	200	mAmps
Continuous Forward Current	I_{Fdc}	300	mAmps
Peak Surge Current (t_{peak} = 1 sec.)	I_{peak}	1.0	Amp
BKC Power Dissipation T_L=50 °C, L = 3/8" from body	P_{tot}	500	mWatts
Operating Temperature Range	T_{Op}	-65 to +200	°C
Storage Temperature Range	T_{St}	-65 to +200	°C

Electrical Characteristics @ 25 °C*	**Symbol**	**Minimum**	**Maximum**	**Unit**
Forward Voltage Drop @ I_F = 10 mA	V_F	***	1.00	Volts
Breakdown Voltage @ I_R = 5 µA	PIV	75		Volts
Breakdown Voltage @ I_R = 100µA	PIV	100		Volts
Reverse Leakage Current @ V_R = 75 V	I_R		5 (100 @ 150 °C)	µA
Capacitance @ V_R = 0 V, f = 1mHz	C_T		4.0	pF
Reverse Recovery time (note 1)	t_{rr}		4.0	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA,Vr = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED

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